

# TGI1213-25LA

### **FEATURES**

- ·BROAD BAND INTERNALLY MATCHED HEMT
- ·HIGH POWER

Pout= 44.0dBm at Pin= 39.0dBm

·HIGH GAIN

GL= 8.0dB at 12.7GHz to 13.2GHz

- •LOW INTERMODULATION DISTORTION WITH WIDE SPACING TONE IM3(Min.)= -25dBc at Pout= 37.0dBm (Single Carrier Level)
- ·HERMETICALLY SEALED PACKAGE



# RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

| CHARACTERISTICS                         | SYMBOL | CONDITIONS   | UNIT | MIN. | TYP. | MAX. |
|---|--------|--|------|------|------|------|
| Output Power                            | Pout   | VDS= 24V<br>IDSset= 1.0A<br>f = 12.7 to 13.2GHz<br>@Pin= 39dBm                                 | dBm  | 43.0 | 44.0 | _    |
| Drain Current                           | IDS1   |  | Α    | _    | 2.5  | 3.0  |
| Power Added Efficiency                  | PAE    |  | %    | _    | 29   |      |
| Linear Gain                             | GL     | @Pin= 20dBm <sup>x</sup>   | dB   | 7.0  | 8.0  | _    |
| Gain Flatness                           | ΔG     |  | dB   | _    | _    | ±0.8 |
| 3rd Order Intermodulation<br>Distortion | IM3    | Two-tone Test<br>Po= 37.0dBm<br>(Single Carrier Level)<br>Δf= 5MHz (IM3)<br>Δf= 150MHz (IM3-2) | dBc  | -25  | -27  |      |
|   | IM3-2  |  | dBc  | -25  | -27  |      |
| Drain Current                           | IDS2   |  | Α    | _    | 1.75 | 2.25 |
| Channel Temperature Rise                | ΔTch   |  | °C   |      | 110  | 140  |

Recommended Gate Resistance(Rg): 13.3  $\Omega$ 

# ELECTRICAL CHARACTERISTICS (Ta= 25°C)

| CHARACTERISTICS               | SYMBOL   | CONDITIONS             | UNIT | MIN. | TYP. | MAX. |
|-------------------------------|----------|------------------------|------|------|------|------|
| Transconductance              | gm       | VDS= 5V<br>IDS= 2.5A   | S    | _    | 2.25 | _    |
| Pinch-off Voltage             | VGSoff   | VDS= 5V<br>IDS= 11.5mA | V    | -1.0 | -4.0 | -6.0 |
| Saturated Drain Current       | IDSS     | VDS= 5V<br>VGS= 0V     | А    | _    | 9.0  | _    |
| Gate-Source Breakdown Voltage | VGSO     | IGS= -5mA              | V    | -10  | _    |      |
| Thermal Resistance            | Rth(c-c) | Channel to Case        | °C/W | _    | 2.8  | 3.2  |

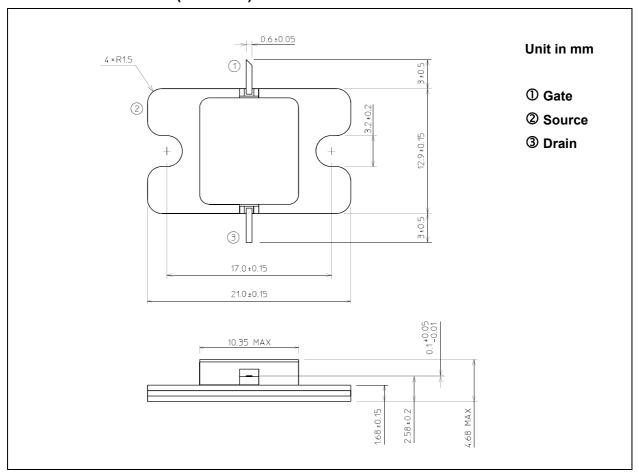
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- MICROWAVE SEMICONDUCTOR TECHNICAL DATA

# ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

| CHARACTERISTICS                    | SYMBOL | UNIT | RATING      |
|------------------------------------|--------|------|-------------|
| Drain-Source Voltage               | VDS    | V    | 50          |
| Gate-Source Voltage                | VGS    | V    | -10         |
| Drain Current                      | IDS    | А    | 7.5         |
| Total Power Dissipation (Tc= 25°C) | PT     | W    | 70          |
| Channel Temperature                | Tch    | °C   | 250         |
| Storage Temperature                | Tstg   | °C   | -65 to +175 |

# **PACKAGE OUTLINE (7-AA07A)**

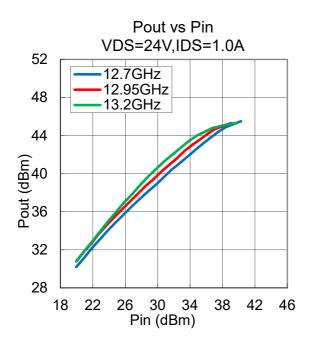


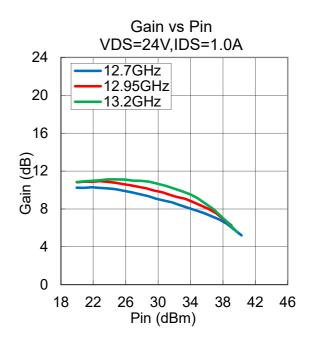
# HANDLING PRECAUTIONS FOR PACKAGE MODEL

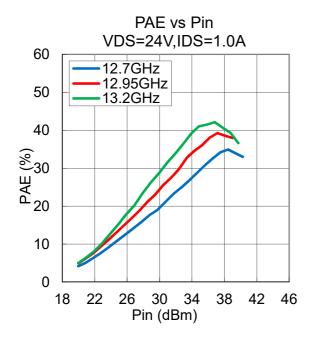
Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C or 3 seconds at 350°C.

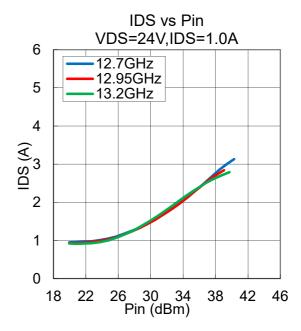
### ·Pout, Gain, PAE, IDS vs. Pin

VDS= 24 V, IDSset= 1.0 A, f= 12.7, 12.95, 13.2GHz, Ta= +25 °C



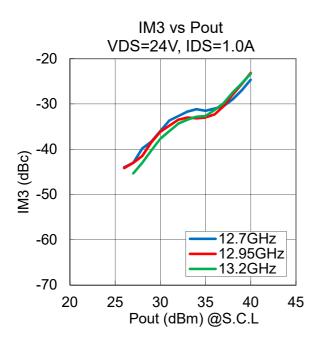


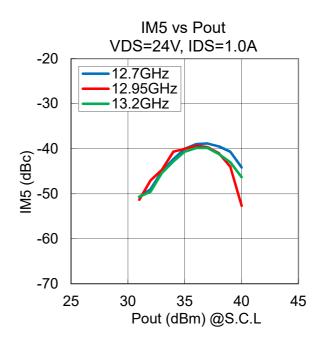




#### ·IM3, IM5 vs. Pout

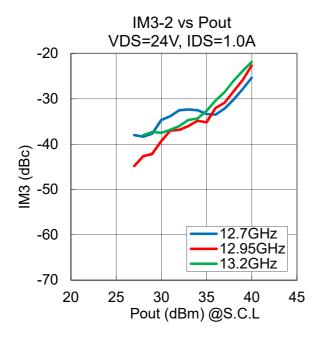
VDS= 24 V, IDSset= 1.0 A, f= 12.7, 12.95, 13.2 GHz,  $\Delta$ f= 5 MHz , Ta= +25  $^{\circ}$ C

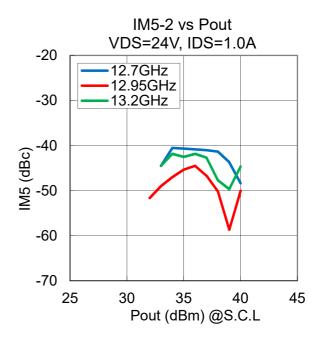




# ·IM3-2, IM5-2 vs. Pout

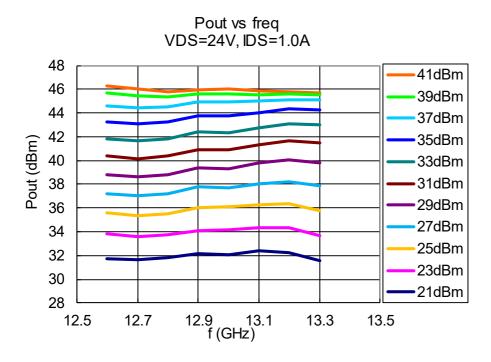
VDS= 24 V, IDSset= 1.0 A, f= 12.7, 12.95, 13.2 GHz,  $\Delta$ f= 150 MHz , Ta= +25  $^{\circ}$ C





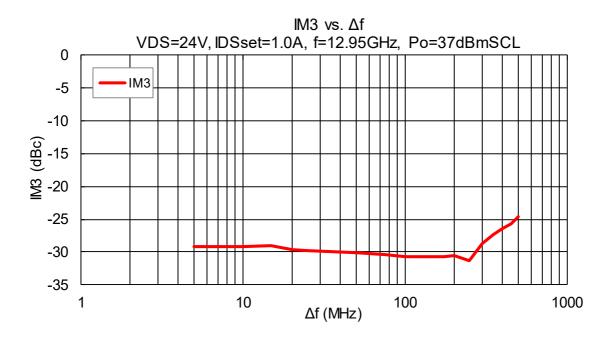
### ·Pout vs. Frequency

VDS= 24 V, IDSset= 1.0 A, Ta= +25 °C



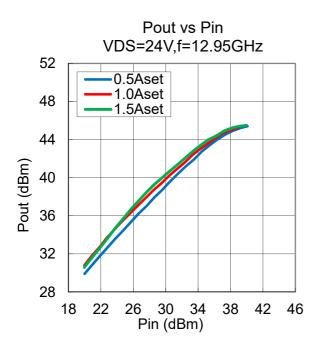
# ·IM3 vs. ∆f (Two tone spacing)

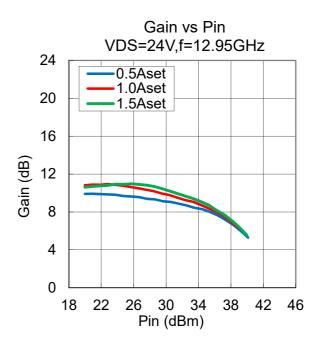
VDS= 24V, IDSset= 1.0A, f= 12.95GHz, Po= 37dBmSCL, Ta= +25°C

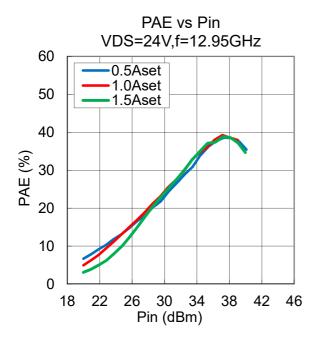


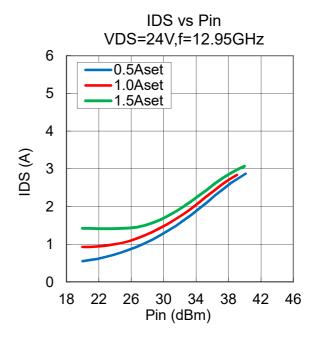
·Pout , Gain , PAE , IDS vs. Pin vs. IDSset

VDS= 24 V, IDSset= 0.5, 1.0, 1.5 A, f= 12.95 GHz, Ta= +25 °C



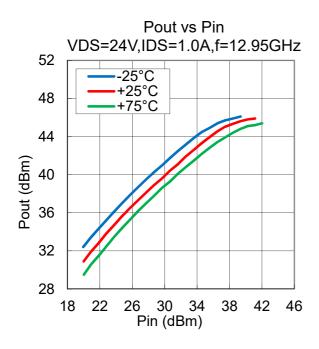


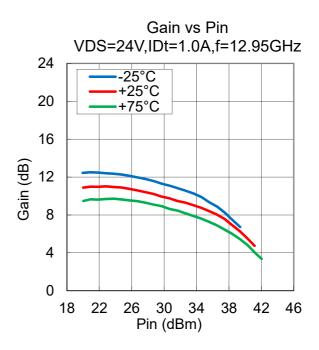


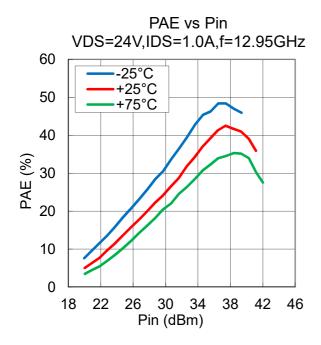


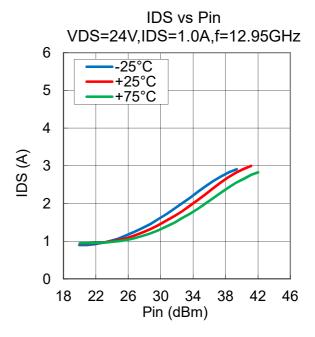
·Pout , Gain , PAE , IDS vs. Pin vs. Temperature

VDS= 24 V, IDSset= 1.0 A, f= 12.95 GHz, Ta= -25, +25, +75 °C





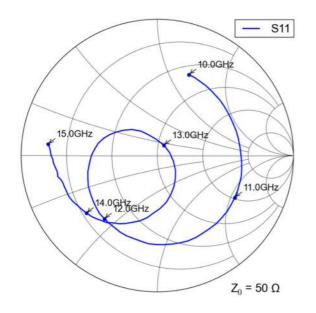


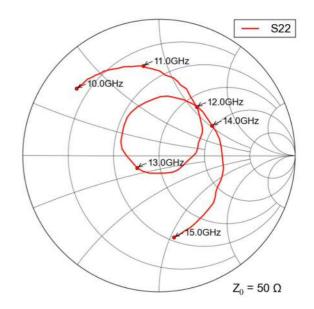


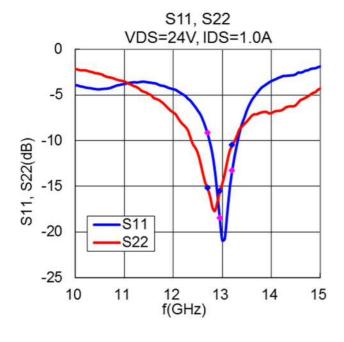


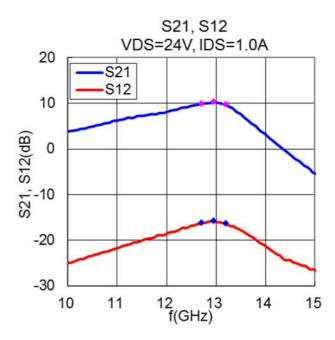
#### ·S-Parameters

VDS= 24 V, IDSset= 1.0 A, f= =10.0 to 15.0 GHz, Ta= +25  $^{\circ}$ C











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